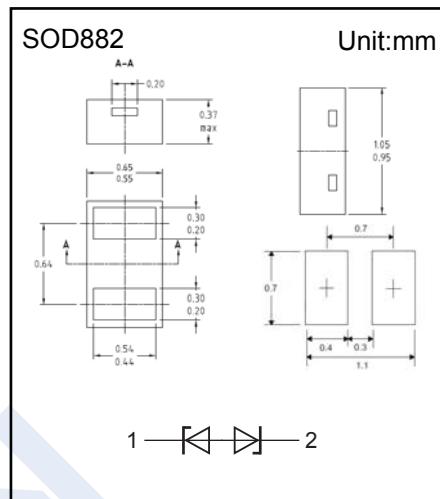


## ESD Protection Diodes

## PESD5V0V1BL

## ■ Features

- Bidirectional ESD protection of one line
- Very low diode capacitance:  $C_d = 11 \text{ pF}$
- Max. peak pulse power:  $P_{PP} = 45 \text{ W}$
- Low clamping voltage:  $V_{CL} = 12.5 \text{ V}$
- Ultra low leakage current:  $I_{RM} < 1 \text{ nA}$
- ESD protection up to 30 kV
- IEC 61000-4-2; level 4 (ESD)
- IEC 61000-4-5 (surge);  $I_{PP} = 4.8 \text{ A}$

■ Absolute Maximum Ratings ( $T_A = 25^\circ\text{C}$ , unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power	$P_{PP}$	45	W
Peak Pulse Current	$I_{PP}$	4.8	A
Electrostatic Discharge Voltage	IEC 61000-4-2 Contact	30	KV
	Machine Model	2	
	MIL-STD-883 HBM	16	
Junction and Storage Temperature Range	$T_j, T_{stg}$	-55 to +150	°C

■ Electrical Characteristics ( $T_A = 25^\circ\text{C}$  unless otherwise specified.)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse standoff voltage	$V_{RWM}$	$I_R = 5 \text{ mA}$			5	V
Breakdown voltage	$V_{BR}$		5.8	6.8	7.8	
Reverse leakage current	$I_{RM}$	$V_{RWM} = 5 \text{ V}$			10	nA
Diode capacitance	$C_d$	$V_R = 0 \text{ V}, f = 1 \text{ MHz}$		11	13	pF
Clamping voltage <sup>*1</sup>	$V_{CL}$	$I_{PP} = 4.8 \text{ A}$			12.5	V
Dynamic resistance <sup>*2</sup>	$r_{dyn}$	$I_R = 10 \text{ A}$	0.2			Ω
Differential resistance	$r_{dif}$	$I_R = 5 \text{ mA}$			35	

<sup>\*1</sup> Non-repetitive current pulse 8/20μs exponential decay waveform according to IEC 61000-4-5.

<sup>\*2</sup> Non-repetitive current pulse, Transmission Line Pulse (TLP)  $t_p = 100 \text{ ns}$ ; square pulse; ANS/IESD STM5.1-2008.

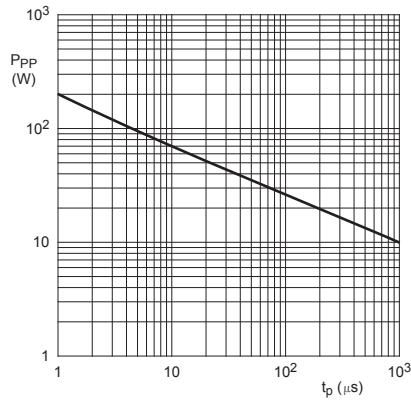
## ■ Marking

Marking	X1
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## ESD Protection Diodes

### PESD5V0V1BL

#### ■ Typical Characteristics



$T_{amb} = 25^\circ\text{C}$

Fig 1. Peak pulse power as a function of exponential pulse duration; typical values

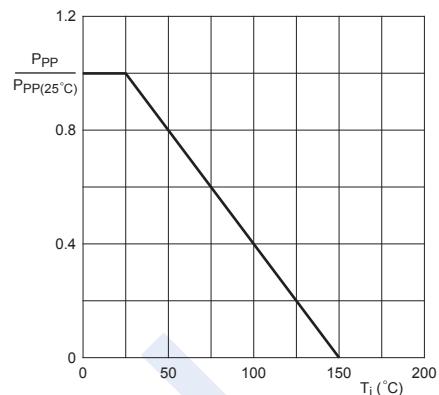
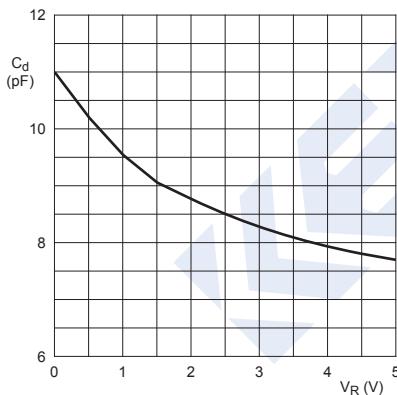


Fig 2. Relative variation of peak pulse power as a function of junction temperature; typical



$f = 1 \text{ MHz}; T_{amb} = 25^\circ\text{C}$

Fig 3. Diode capacitance as a function of reverse voltage; typical values

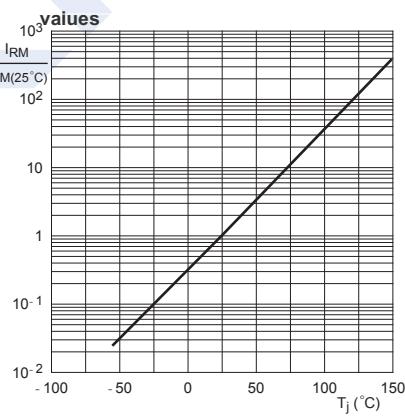


Fig 4. Relative variation of reverse leakage current as a function of junction temperature; typical values

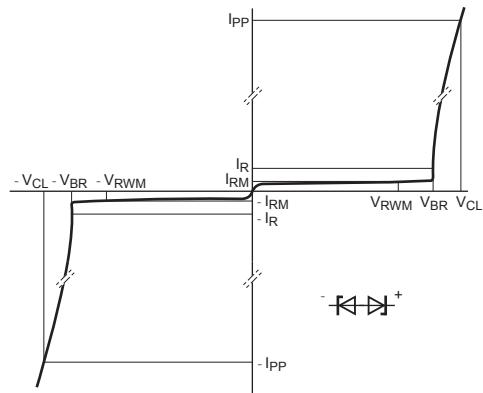


Fig 5. V-I characteristics for a bidirectional ESD protection diode